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N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16323Q3C

FEATURES

- DualCool™ Package
- Optimized for 5V Gate Drive
- Ultra Low Q_q and Q_{qd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 3.3-mm × 3.3-mm Plastic Package

APPLICATIONS

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Control or Synchronous FET Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion and optimized for 5V gate drive applications.

PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage 25			V
Q_g	Gate Charge Total (4.5V) 6.2			nC
Q_{gd}	Gate Charge Gate to Drain	1.1		
		$V_{GS} = 3V$	5.4	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V$	4.4	mΩ
		V _{GS} = 8V 3.8		mΩ
V_{th}	Threshold Voltage 1.1		V	

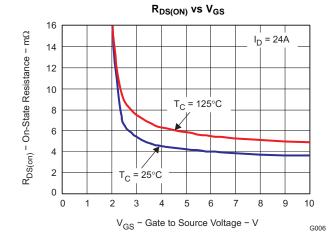
ORDERING INFORMATION

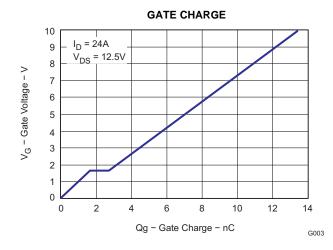
Device	Package	Media	Qty	Ship
CSD16323Q3C	SON 3.3-mm × 3.3-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+10 / -8	V
	Continuous Drain Current, T _C = 25°C	60	Α
I _D	Continuous Drain Current ⁽¹⁾	21	Α
I_{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	112	Α
P_D	Power Dissipation ⁽¹⁾	3	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D = 50A$, $L = 0.1mH$, $R_G = 25\Omega$	125	mJ

- (1) Typical $R_{\theta JA}=43^{\circ} C/W$ when mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%





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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	naracteristics					
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 20V			1	μА
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10/-8V$			100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.9	1.1	1.4	V
		$V_{GS} = 3V$, $I_D = 24A$		5.4	7.2	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 24A$		4.4	5.5	mΩ
		$V_{GS} = 8V, I_{D} = 24A$		3.8	4.5	mΩ
9 _{fs}	Transconductance	V _{DS} = 12.5V, I _D = 24A		108		S
Dynamic	Characteristics				•	
C _{ISS}	Input Capacitance			1020	1300	рF
Coss	Output Capacitance	V _{GS} = 0V, V _{DS} = 12.5V, f = 1MHz		740	960	pF
C _{RSS}	Reverse Transfer Capacitance			50	65	pF
R _g	Series Gate Resistance			1.4	2.8	Ω
Qg	Gate Charge Total (4.5V)			6.2	8.4	nC
Q_{gd}	Gate Charge Gate to Drain	V 42.5V L 24A		1.1		nC
Q _{gs}	Gate Charge Gate to Source	$V_{DS} = 12.5V, I_{D} = 24A$		1.8		nC
Qg(th)	Gate Charge at Vth			1		nC
Q _{OSS}	Output Charge	$V_{DS} = 12.5V, V_{GS} = 0V$		14		nC
t _{d(on)}	Turn On Delay Time			5.3		ns
t _r	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V I_{D} = 24A$		15		ns
t _{d(off)}	Turn Off Delay Time	$R_G = 2\Omega$		13		ns
t _f	Fall Time			6.3		ns
Diode Cl	haracteristics					
V_{SD}	Diode Forward Voltage	I _S = 24A, V _{GS} = 0V		0.85	1	V
Q _{rr}	Reverse Recovery Charge	$V_{DD} = 12.5V$, $I_F = 24A$, $di/dt = 300A/\mu s$		21		nC
t _{rr}	Reverse Recovery Time	$V_{DD} = 12.5V$, $I_F = 24A$, $di/dt = 300A/\mu s$		16		ns

THERMAL CHARACTERISTICS

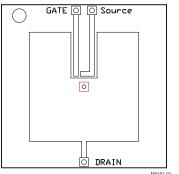
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	MIN	TYP	MAX	UNIT
$\theta_{\text{JC(top)}}$	Junction-to-case (top) thermal resistance			3.5	°C/W
$\theta_{\text{JC(bot)}}$	Junction-to-case (bottom) thermal resistance (1)			2.7	°C/W
θJA	Junction to Ambient thermal resistance (1) (2)			58	°C/W

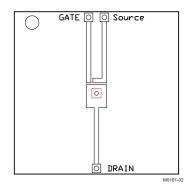
 ⁽¹⁾ R_{θJC} is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.
 (2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.

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Max $R_{\theta JA} = 58^{\circ} C/W$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 162^{\circ} C/W$ when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

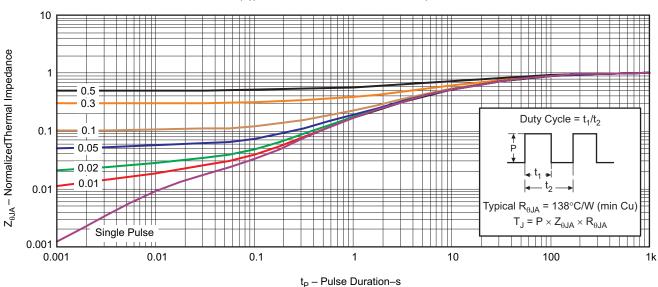


Figure 1. Transient Thermal Impedance

G012

TEXAS INSTRUMENTS

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

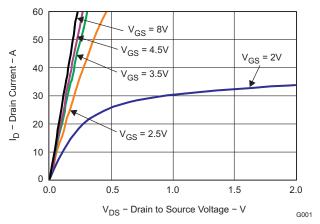


Figure 2. Saturation Characteristics

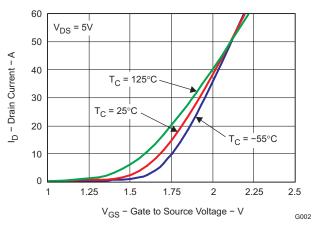


Figure 3. Transfer Characteristics

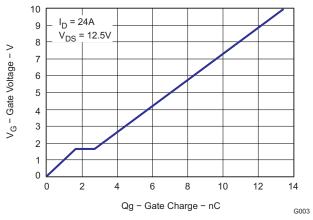


Figure 4. Gate Charge

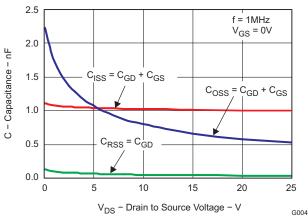


Figure 5. Capacitance

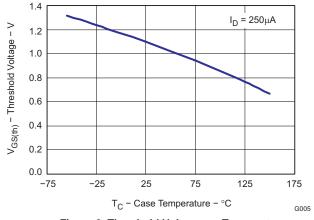


Figure 6. Threshold Voltage vs. Temperature

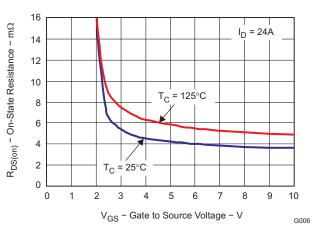


Figure 7. On-State Resistance vs. Gate-to-Source Voltage

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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

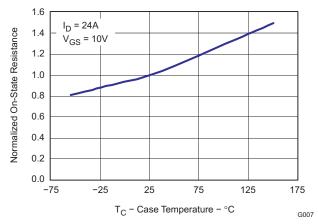


Figure 8. Normalized On-State Resistance vs. Temperature

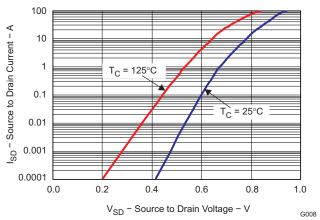


Figure 9. Typical Diode Forward Voltage

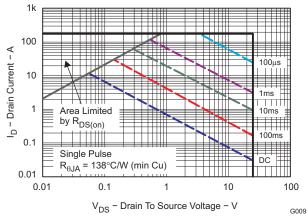


Figure 10. Maximum Safe Operating Area

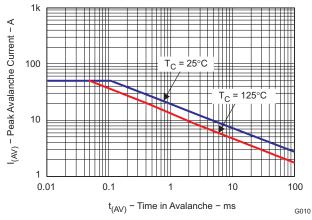


Figure 11. Single Pulse Unclamped Inductive Switching

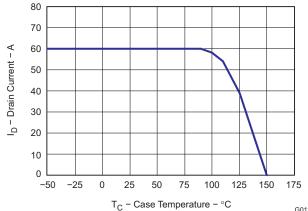
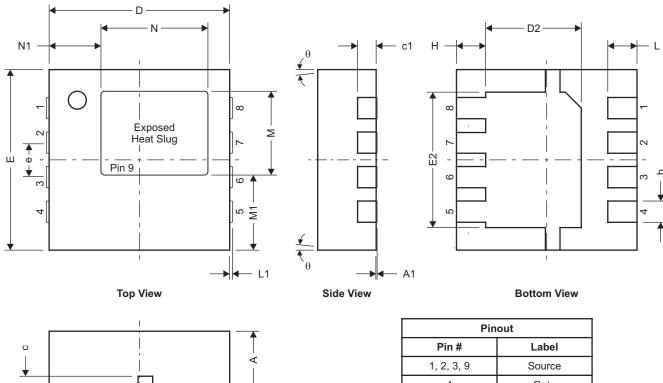


Figure 12. Maximum Drain Current vs. Temperature



MECHANICAL DATA

Q3C Package Dimensions



Pinout				
Pin #	Label			
1, 2, 3, 9	Source			
4	Gate			
5, 6, 7, 8	Drain			

Front View

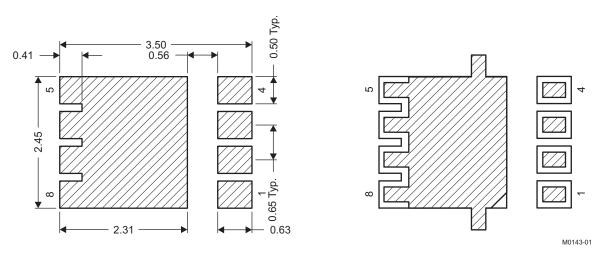
M0198-01

DIM		MILLIMETERS	3	INCHES				
	MIN	NOM	MAX	MIN	NOM	MAX		
Α	0.950	1.000	1.100	0.037	0.039	0.043		
A1	0.000	0.000	0.050	0.000	0.000	0.002		
b	0.280	0.340	0.400	0.011	0.013	0.016		
С	0.150	0.200	0.250	0.006	0.008	0.010		
c1	0.150	0.200	0.250	0.006	0.008	0.010		
D	3.200	3.300	3.400	0.126	0.130	0.134		
D2	1.650	1.750	1.800	0.065	0.069	0.071		
Е	3.200	3.300	3.400	0.126	0.130	0.134		
E2	2.350	2.450	2.550	0.093	0.096	0.100		
е		0.650 TYP			0.026			
Н	0.35	0.450	0.550	0.014	0.018	0.022		
L	0.35	0.450	0.550	0.014	0.018	0.022		
L1	-	_	-	_	_	_		
M	1.561	1.661	1.761	0.061	0.065	0.069		
M1	1.130	1.230	1.330	0.044	0.048	0.052		
N	1.854	1.954	2.054	0.073	0.077	0.081		
N1	0.846	0.946	1.046	0.033	0.037	0.041		
θ	-	_	-	_	_	_		



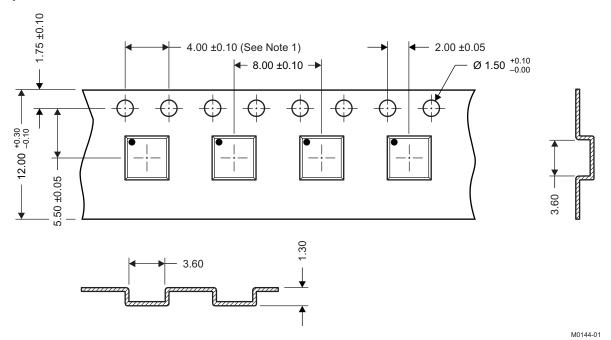
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Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q3 Tape and Reel Information



NOTES: 1. 10-sprocket hole-pitch cumulative tolerance ±0.2

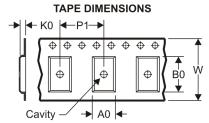
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and convection) PbF reflow compatible

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





Α	0	Dimension designed to accommodate the component width
В	0	Dimension designed to accommodate the component length
		Dimension designed to accommodate the component thickness
٧	٧	Overall width of the carrier tape
ГР	1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16323Q3C	SON	DQV	8	2500	330.0	12.8	3.6	3.6	1.2	8.0	12.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD16323Q3C	SON	DQV	8	2500	335.0	335.0	32.0

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